

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	699	antenna near2 (interconnect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:55
L2	42573	peripheral near3 (substrate or chip)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:55
L3	1	1 same 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:55
L4	5	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:55
L5	311	antenna same 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:57
L6	31	inductor and 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 15:57
L7	1	("20010053672").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/22 16:01
L8	1	7 and (antenna near5 ("I" or "L" or "U" or (multiple adj2 loop)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/22 16:02
S1	1	("20060157798").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/16 13:42

S2	3	low-capacitance adj2 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:42
S3	1	S1 and S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:43
S4	0	(low-permittivity adj2 insulating) and S1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:48
S5	1	(low-permittivity adj2 insulating) and S1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:48
S6	1787	openings near3 (randomly or random)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:58
S7	1	S1 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 13:58
S8	1	S1 and (linear adj2 current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 14:00
S9	0	S1 and (high-permittivity adj2 region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 14:04

S10	0	S1 and (high adj2 permittivity adj2 region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 14:04
S11	1	S1 and (magnetic adj2 rods)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 14:12
S12	1	S1 and (inner adj2 wall)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 14:15
S13	1	("20060157798").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/16 16:17
S14	1	S13 and (magnetic adj2 rod)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:17
S15	15669	inductor same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:23
S16	2865	S15 same transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:23
S17	10	(interlevel adj2 dielectric) same S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:24
S18	1513	permittivity near2 (insulator or insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:26

S19	10	S18 near5 opening	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:26
S20	62	(interlevel adj2 dielectric) and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:27
S21	54	S20 and (interconnect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:27
S22	45	S21 not S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:28
S23	18	("20020017673"   "20020072189"   "4891684"   "5780334"   "5949098"   "6117747"   "6124198"   "6255186"   "6346741"   "6348373"   "6410955"   "6524926"   "6531730"   "6730974"   "6735726"   "6740922"   "6747307"   "6822312"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/16 16:31
S24	1879	permeability near5 openings	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:35
S25	3	S15 and S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:36
S26	4471	porous adj2 (insulating or insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:38

S27	2412	organic adj2 siloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:40
S28	2431	msq	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:40
S29	4180	SiOC or SiOCH	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:40
S30	410	S29 near3 carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:41
S31	9459	S26 or S27 or S28 or S30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:41
S32	79	S31 near5 openings	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:41
S33	1	S15 and S32	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 16:41
S34	166496	(iron near2 cobalt) or (Fe near2 Co)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:37

S35	106267	(Ni near2 co)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:37
S36	37125	(Fe near2 Al)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:37
S37	241486	S34 or S35 or S36	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S38	116	S37 near5 opening	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S39	15669	S15 same inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S40	0	S38 and inducotr	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S41	45	S38 and inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S42	45	S41 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38

S43	0	(interlevel adj2 dielectric) and S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:38
S44	0	S42 and (interconnect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/16 17:39
S45	4284	low adj2 permittivity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:06
S46	1479	S45 near2 (insulator or insulating or material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:07
S47	4471	porous adj2 (insulating or insulator)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:07
S48	2412	organic adj2 siloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:07
S49	4180	SiOC or SiOCH	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:07
S50	410	S49 near3 carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:08

S51	8653	S46 or S47 or S48 or S50	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:08
S52	197	S51 near5 (trench or opening or groove)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:08
S53	104	S52 same4 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:17
S54	2	S53 same4 inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:17
S55	4	S53 and inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:17
S56	2	S55 not S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:17
S57	135	S52 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:19
S58	4	S57 and inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:20



S59	0	S58 not S55	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:20
S60	7371	((silicon adj2 oxide) near2 carbon) or "SiOC"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:25
S61	4245	((silicon adj2 oxide) near2 (fluorine or "F")) or "SiOF"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:25
S62	10539	S60 or S61	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:26
S63	280	S62 near5 (trench or opening or groove)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:26
S64	179	S63 same4 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:26
S65	0	S64 same4 inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:26
S66	6	S64 and inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:26

S67	246	S63 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:28
S68	9	S67 and inductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:28
S69	3	S68 not S66	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:28
S70	1791	S62 near2 (insulator or insulating or material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:29
S71	18	S70 near10 (benefit or advantage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/17 12:29

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